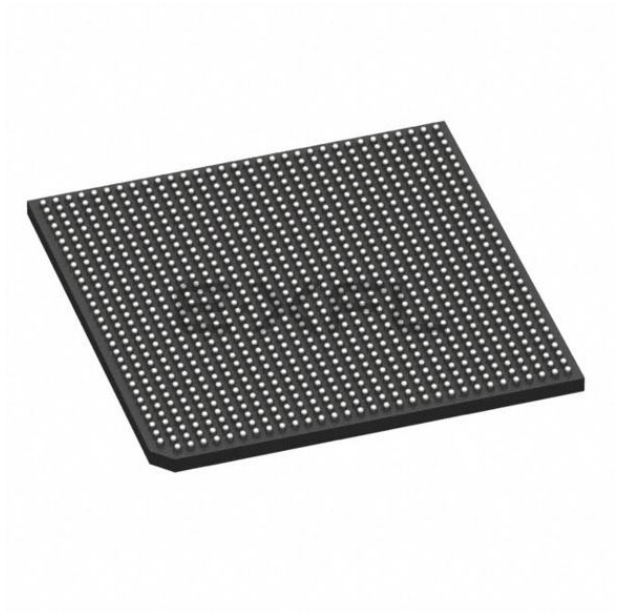

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	2 Core, 32-Bit
Speed	1.5GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR2, DDR3
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.5V, 1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	1023-BFBGA, FCBGA
Supplier Device Package	1023-FCBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/ppc8572epxavnc

  - Three inbound windows plus a configuration window on PCI Express
  - Four inbound windows plus a default window on Serial RapidIO®
  - Four outbound windows plus default translation for PCI Express
  - Eight outbound windows plus default translation for Serial RapidIO with segmentation and sub-segmentation support

- Two 64-bit DDR2/DDR3 memory controllers
  - Programmable timing supporting DDR2 and DDR3 SDRAM
  - 64-bit data interface per controller
  - Four banks of memory supported, each up to 4 Gbytes, for a maximum of 16 Gbytes per controller
  - DRAM chip configurations from 64 Mbits to 4 Gbits with x8/x16 data ports
  - Full ECC support
  - Page mode support
    - Up to 32 simultaneous open pages for DDR2 or DDR3
  - Contiguous or discontiguous memory mapping
  - Cache line, page, bank, and super-bank interleaving between memory controllers
  - Read-modify-write support for RapidIO atomic increment, decrement, set, and clear transactions
  - Sleep mode support for self-refresh SDRAM
  - On-die termination support when using DDR2 or DDR3
  - Supports auto refreshing
  - On-the-fly power management using CKE signal
  - Registered DIMM support
  - Fast memory access through JTAG port
  - 1.8-V SSTL_1.8 compatible I/O
  - Support 1.5-V operation for DDR3. The detail is TBD pending on official release of appropriate industry specifications.
  - Support for battery-backed main memory
- Programmable interrupt controller (PIC)
  - Programming model is compliant with the OpenPIC architecture.
  - Supports 16 programmable interrupt and processor task priority levels
  - Supports 12 discrete external interrupts
  - Supports 4 message interrupts per processor with 32-bit messages
  - Supports connection of an external interrupt controller such as the 8259 programmable interrupt controller
  - Four global high resolution timers/counters per processor that can generate interrupts
  - Supports a variety of other internal interrupt sources

- Supports fully nested interrupt delivery
- Interrupts can be routed to external pin for external processing.
- Interrupts can be routed to the e500 core's standard or critical interrupt inputs.
- Interrupt summary registers allow fast identification of interrupt source.

- Integrated security engine (SEC) optimized to process all the algorithms associated with IPSec, IKE, SSL/TLS, SRTP, 802.16e, and 3GPP
  - Four crypto-channels, each supporting multi-command descriptor chains
    - Dynamic assignment of crypto-execution units through an integrated controller
    - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
  - PKEU—public key execution unit
    - RSA and Diffie-Hellman; programmable field size up to 4096 bits
    - Elliptic curve cryptography with F_2m and F(p) modes and programmable field size up to 1023 bits
  - DEU—Data Encryption Standard execution unit
    - DES, 3DES
    - Two key (K1, K2, K1) or three key (K1, K2, K3)
    - ECB, CBC and OFB-64 modes for both DES and 3DES
  - AESU—Advanced Encryption Standard unit
    - Implements the Rijndael symmetric key cipher
    - ECB, CBC, CTR, CCM, GCM, CMAC, OFB-128, CFB-128, and LRW modes
    - 128-, 192-, and 256-bit key lengths
  - AFEU—ARC four execution unit
    - Implements a stream cipher compatible with the RC4 algorithm
    - 40- to 128-bit programmable key
  - MDEU—message digest execution unit
    - SHA-1 with 160-bit message digest
    - SHA-2 (SHA-256, SHA-384, SHA-512)
    - MD5 with 128-bit message digest
    - HMAC with all algorithms
  - KEU—Kasumi execution unit
    - Implements F8 algorithm for encryption and F9 algorithm for integrity checking
    - Also supports A5/3 and GEA-3 algorithms
  - RNG—random number generator
  - XOR engine for parity checking in RAID storage applications
  - CRC execution unit
    - CRC-32 and CRC-32C
- Pattern Matching Engine with DEFLATE decompression

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings[1]

Characteristic		Symbol	Range	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.21	V	—
PLL supply voltage		AV_{DD}	–0.3 to 1.21	V	—
Core power supply for SerDes transceivers		SV_{DD}	–0.3 to 1.21	V	—
Pad power supply for SerDes transceivers		XV_{DD}	–0.3 to 1.21	V	—
DDR SDRAM Controller I/O supply voltage	DDR2 SDRAM Interface	GV_{DD}	–0.3 to 1.98	V	—
	DDR3 SDRAM Interface	—	–0.3 to 1.65		—
Three-speed Ethernet I/O, FEC management interface, MII management voltage		LV_{DD} (for eTSEC1 and eTSEC2) TV_{DD} (for eTSEC3 and eTSEC4, FEC)	–0.3 to 3.63 –0.3 to 2.75 –0.3 to 3.63 –0.3 to 2.75	V — —	2 2
DUART, system control and power management, I^2C, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	—
Local bus and GPIO I/O voltage		BV_{DD}	–0.3 to 3.63 –0.3 to 2.75 –0.3 to 1.98	V	—
Input voltage	DDR2 and DDR3 SDRAM interface signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	3
	DDR2 and DDR3 SDRAM interface reference	$MV_{REF}n$	–0.3 to (GV_{DD}/2 + 0.3)	V	—
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	–0.3 to (LV_{DD} + 0.3) –0.3 to (TV_{DD} + 0.3)	V	3
	Local bus and GPIO signals	BV_{IN}	–0.3 to (BV_{DD} + 0.3)	—	—
	DUART, SYSCLK, system control and power management, I^2C, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	3
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:

1. Functional operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. The 3.63V maximum is only supported when the port is configured in GMII, MII, RMII or TBI modes; otherwise the 2.75V maximum applies. See Section 8.2, “FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications,” for details on the recommended operating conditions per protocol.
3. (M,L,O)V_{IN} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.

Table 14 provides the current draw characteristics for $MV_{REF}n$.

Table 14. Current Draw Characteristics for MV_{REF} *n*

Parameter / Condition		Symbol	Min	Max	Unit	Note
Current draw for $MV_{REF}n$	DDR2 SDRAM	$I_{MVREF}n$	—	1500	µA	1
	DDR3 SDRAM			1250		

1. The voltage regulator for $MV_{REF}n$ must be able to supply up to 1500 µA or 1250 uA current for DDR2 or DDR3, respectively.

6.2 DDR2 and DDR3 SDRAM Interface AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM controller interface. The DDR controller supports both DDR2 and DDR3 memories. Note that although the minimum data rate for most off-the-shelf DDR3 DIMMs available is 800 MHz, JEDEC specification does allow the DDR3 to run at the data rate as low as 606 MHz. Unless otherwise specified, the AC timing specifications described in this section for DDR3 is applicable for data rate between 606 MHz and 800 MHz, as long as the DC and AC specifications of the DDR3 memory to be used are compliant to both JEDEC specifications as well as the specifications and requirements described in this MPC8572E hardware specifications document.

6.2.1 DDR2 and DDR3 SDRAM Interface Input AC Timing Specifications

Table 15, Table 16, and Table 17 provide the input AC timing specifications for the DDR controller when interfacing to DDR2 and DDR3 SDRAM.

Table 15. DDR2 SDRAM Interface Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with GV_{DD} of 1.8 V ± 5%

Parameter		Symbol	Min	Max	Unit	Notes
AC input low voltage	>=667 MHz	V_{ILAC}	—	$MV_{REF}n$ – 0.20	V	—
	<= 533 MHz		—	$MV_{REF}n$ – 0.25		
AC input high voltage	>=667 MHz	V_{IHAC}	$MV_{REF}n$ + 0.20	—	V	—
—	<= 533 MHz		$MV_{REF}n$ + 0.25	—		

Table 16. DDR3 SDRAM Interface Input AC Timing Specifications for 1.5-V Interface

At recommended operating conditions with GV_{DD} of 1.5 V ± 5%. DDR3 data rate is between 606 MHz and 800 MHz.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{ILAC}	—	$MV_{REF}n$ – 0.175	V	—
AC input high voltage	V_{IHAC}	$MV_{REF}n$ + 0.175	—	V	—

Table 18. DDR2 and DDR3 SDRAM Interface Output AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of 1.8 V ± 5% for DDR2 or 1.5 V ± 5% for DDR3.

Parameter	Symbol [1]	Min	Max	Unit	Notes
533 MHz		538	—		
400 MHz		700	—		
MDQS preamble start	t_{DDKHMP}			ns	6
800 MHz		$-0.5 \times t_{MCK} - 0.375$	$-0.5 \times t_{MCK} + 0.375$		
<= 667 MHz		$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$		
MDQS epilogue end	t_{DDKHME}			ns	6
800 MHz		–0.375	0.375		
<= 667 MHz	t_{DDKHME}	–0.6	0.6	ns	6

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the MDQS override bits (called WR_DATA_DELAY) in the TIMING_CFG_2 register. This typically be set to the same delay as in DDR_SDRAM_CLK_CNTL[CLK_ADJUST]. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8572E PowerQUICC™ III Integrated Host Processor Family Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

NOTE

For the ADDR/CMD setup and hold specifications in Table 18, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.

Figure 6 provides the AC test load for the DDR2 and DDR3 Controller bus.

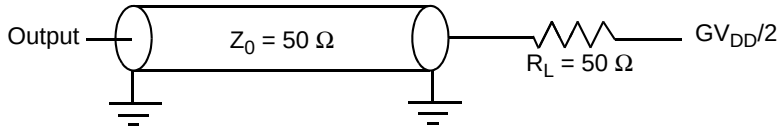
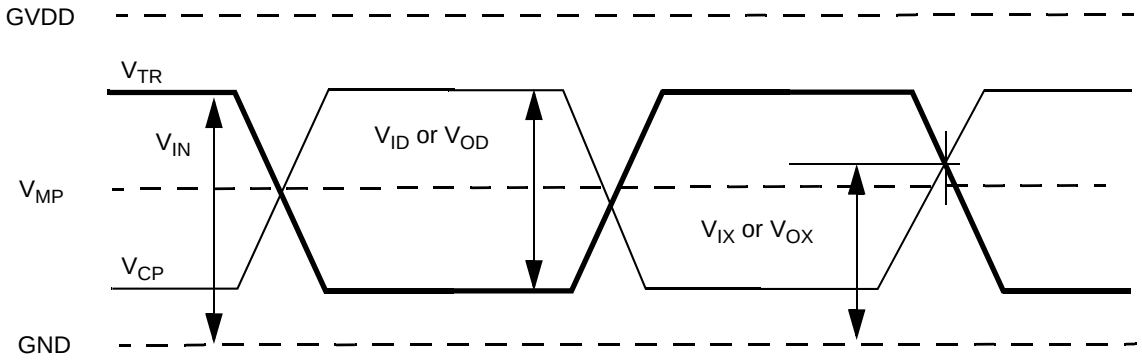


Figure 6. DDR2 and DDR3 Controller bus AC Test Load

6.2.3 DDR2 and DDR3 SDRAM Differential Timing Specifications

This section describes the DC and AC differential electrical specifications for the DDR2 and DDR3 SDRAM controller interface of the MPC8572E.



NOTE

VID specifies the input differential voltage |VTR -VCP| required for switching, where VTR is the true input signal (such as MCK or MDQS) and VCP is the complementary input signal (such as $\overline{\text{MCK}}$ or $\overline{\text{MDQS}}$).

Table 19 provides the differential specifications for the MPC8572E differential signals MDQS/$\overline{\text{MDQS}}$ and MCK/$\overline{\text{MCK}}$ when in DDR2 mode.

Table 19. DDR2 SDRAM Differential Electrical Characteristics

Parameter/Condition	Symbol	Min	Max	Unit	Notes
DC Input Signal Voltage	V_{IN}	–0.3	GV_{DD} + 0.3	V	—
DC Differential Input Voltage	V_{ID}	—	—	mV	—
AC Differential Input Voltage	V_{IDAC}	—	—	mV	—
DC Differential Output Voltage	V_{OH}	—	—	mV	—
AC Differential Output Voltage	V_{OHAC}	JEDEC: 0.5	JEDEC: GV_{DD} + 0.6	V	—
AC Differential Cross-point Voltage	V_{IXAC}	—	—	mV	—
Input Midpoint Voltage	V_{MP}	—	—	mV	—

Table 24. MII, GMII, RMII, RGMII, TBI, RTBI, and FIFO DC Electrical Characteristics (continued)

Parameters	Symbol	Min	Max	Unit	Notes
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	10	µA	1, 2,3
Input low current (V_{IN} = GND)	I_{IL}	–15	—	µA	3

Note:

1 LV_{DD} supports eTSECs 1 and 2.
2 TV_{DD} supports eTSECs 3 and 4 or FEC.
3 Note that the symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1.

8.2 FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications

The AC timing specifications for FIFO, GMII, MII, TBI, RGMII, RMII and RTBI are presented in this section.

8.2.1 FIFO AC Specifications

The basis for the AC specifications for the eTSEC's FIFO modes is the double data rate RGMII and RTBI specifications, because they have similar performance and are described in a source-synchronous fashion like FIFO modes. However, the FIFO interface provides deliberate skew between the transmitted data and source clock in GMII fashion.

When the eTSEC is configured for FIFO modes, all clocks are supplied from external sources to the relevant eTSEC interface. That is, the transmit clock must be applied to the eTSEC*n*'s TSEC*n*_TX_CLK, while the receive clock must be applied to pin TSEC*n*_RX_CLK. The eTSEC internally uses the transmit clock to synchronously generate transmit data and outputs an echoed copy of the transmit clock back on the TSEC*n*_GTX_CLK pin (while transmit data appears on TSEC*n*_TXD[7:0], for example). It is intended that external receivers capture eTSEC transmit data using the clock on TSEC*n*_GTX_CLK as a source-synchronous timing reference. Typically, the clock edge that launched the data can be used, because the clock is delayed by the eTSEC to allow acceptable set-up margin at the receiver. Note that there is a relationship between the maximum FIFO speed and the platform (CCB) frequency. For more information see Section 4.5, "Platform to eTSEC FIFO Restrictions."

Table 25 and Table 26 summarize the FIFO AC specifications.

Table 25. FIFO Mode Transmit AC Timing Specification

At recommended operating conditions with LV_{DD}/TV_{DD} of 2.5V ± 5%

Parameter/Condition	Symbol	Min	Typ	Max	Unit
TX_CLK, GTX_CLK clock period[1]	t_{FIT}	5.3	8.0	100	ns
TX_CLK, GTX_CLK duty cycle	t_{FITH}/t_{FIT}	45	50	55	%

Figure 11 shows the GMII receive AC timing diagram.

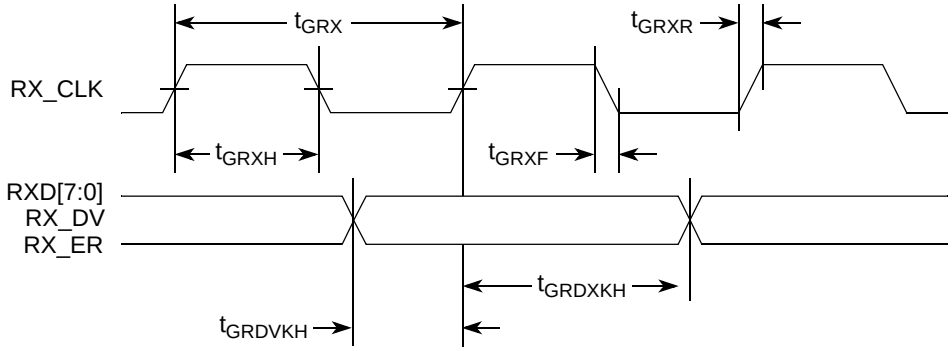


Figure 11. GMII Receive AC Timing Diagram

8.2.3 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.3.1 MII Transmit AC Timing Specifications

Table 29 provides the MII transmit AC timing specifications.

Table 29. MII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/TV_{DD} of 2.5/ 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}[2]	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise (20%-80%)	t_{MTXR}[2]	1.0	—	4.0	ns
TX_CLK data clock fall (80%-20%)	t_{MTXF}[2]	1.0	—	4.0	ns

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.

Figure 18 shows the RGMII and RTBI AC timing and multiplexing diagrams.

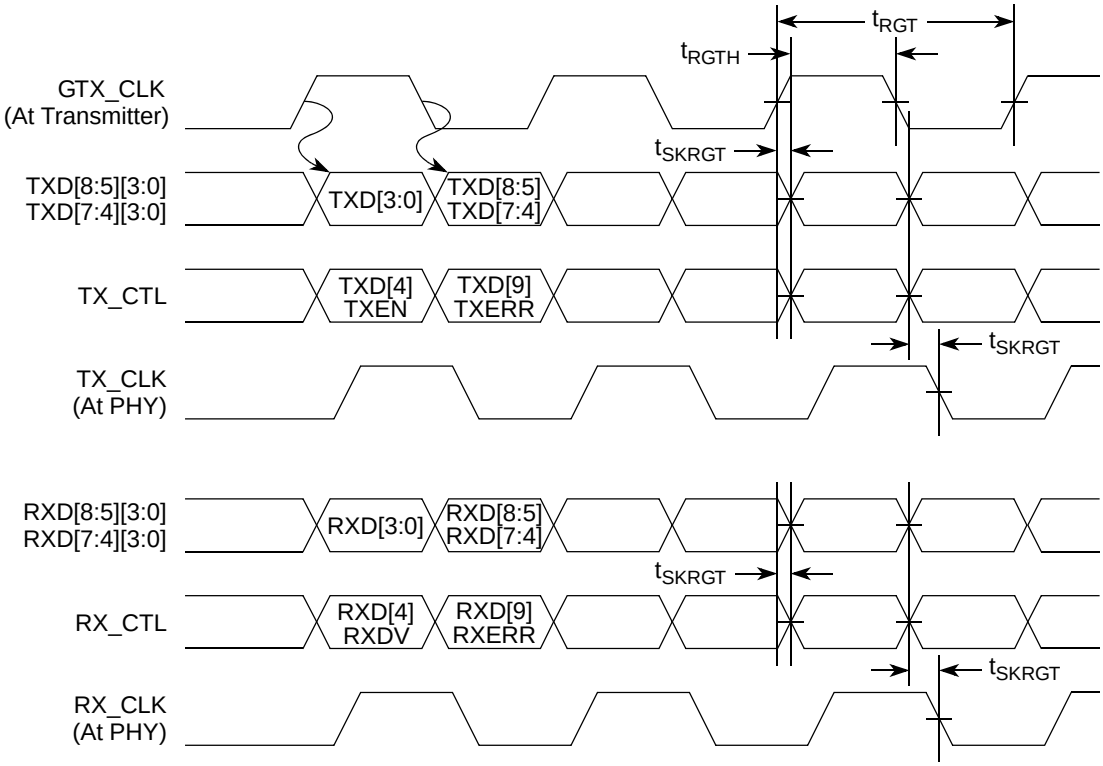


Figure 18. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.2.7 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

8.2.7.1 RMII Transmit AC Timing Specifications

Table 35 shows the RMII transmit AC timing specifications.

Table 35. RMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/TV_{DD} of 2.5/ 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
TSECn_TX_CLK clock period	t_{RMT}	15.0	20.0	25.0	ns
TSECn_TX_CLK duty cycle	t_{RMTH}	35	50	65	%
TSECn_TX_CLK peak-to-peak jitter	t_{RMTJ}	—	—	250	ps
Rise time TSECn_TX_CLK (20%–80%)	t_{RMTR}	1.0	—	2.0	ns
Fall time TSECn_TX_CLK (80%–20%)	t_{RMTF}	1.0	—	2.0	ns

8.3.3 SGMII Transmitter and Receiver DC Electrical Characteristics

Table 38 and Table 39 describe the SGMII SerDes transmitter and receiver AC-Coupled DC electrical characteristics. Transmitter DC characteristics are measured at the transmitter outputs (SD2_TX[n] and $\overline{\text{SD2\_TX[n]}}$) as depicted in Figure 23.

Table 38. SGMII DC Transmitter Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Supply Voltage	XV_{DD_SRDS2}	1.045	1.1	1.155	V	—
Output high voltage	VOH	—	—	$XV_{DD\_SRDS2-Typ}/2 + \lvert\overline{V_{OD}}\rvert_{-max}/2$	mV	1
Output low voltage	VOL	$XV_{DD\_SRDS2-Typ}/2 - \lvert V_{OD}\rvert_{-max}/2$	—	—	mV	1
Output ringing	V_{RING}	—	—	10	%	—
Output differential voltage[2, 3, 5]	$\lvert V_{OD}\rvert$	359	550	791	mV	Equalization setting: 1.0x
		329	505	725		Equalization setting: 1.09x
		299	458	659		Equalization setting: 1.2x
		270	414	594		Equalization setting: 1.33x
		239	367	527		Equalization setting: 1.5x
		210	322	462		Equalization setting: 1.71x
		180	275	395		Equalization setting: 2.0x
Output offset voltage	V_{OS}	473	550	628	mV	1, 4
Output impedance (single-ended)	R_O	40	—	60	Ω	—
Mismatch in a pair	ΔR_O	—	—	10	%	—
Change in V_{OD} between “0” and “1”	$\Delta \lvert V_{OD}\rvert$	—	—	25	mV	—

Table 45. MII Management AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD}/TV_{DD} of 3.3 V ± 5% or 2.5 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit	Notes
ECn_MDIO to ECn_MDC setup time	t_{MDDVKH}	5	—	—	ns	—
ECn_MDIO to ECn_MDC hold time	t_{MDDXKH}	0	—	—	ns	—
ECn_MDC rise time	t_{MDCR}	—	—	10	ns	4
ECn_MDC fall time	t_{MDHF}	—	—	10	ns	4

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the eTSEC system clock speed, which is half of the Platform Frequency (f_{CCB}). The actual ECn_MDC output clock frequency for a specific eTSEC port can be programmed by configuring the MgmtClk bit field of MPC8572E's MIIMCFG register, based on the platform (CCB) clock running for the device. The formula is: Platform Frequency (CCB)/(2*Frequency Divider determined by MIICFG[MgmtClk] encoding selection). For example, if MIICFG[MgmtClk] = 000 and the platform (CCB) is currently running at 533 MHz, f_{MDC} = 533/(2*4*8) = 533/64 = 8.3 MHz. That is, for a system running at a particular platform frequency (f_{CCB}), the ECn_MDC output clock frequency can be programmed between maximum $f_{MDC} = f_{CCB}/64$ and minimum $f_{MDC} = f_{CCB}/448$. Refer to MPC8572E reference manual's MIIMCFG register section for more detail.
3. The maximum ECn_MDC output clock frequency is defined based on the maximum platform frequency for MPC8572E (600 MHz) divided by 64, while the minimum ECn_MDC output clock frequency is defined based on the minimum platform frequency for MPC8572E (400 MHz) divided by 448, following the formula described in Note 2 above. The typical ECn_MDC output clock frequency of 2.5 MHz is shown for reference purpose per IEEE 802.3 specification.
4. Guaranteed by design.
5. t_{plb_clk} is the platform (CCB) clock.

Figure 28 shows the MII management AC timing diagram.

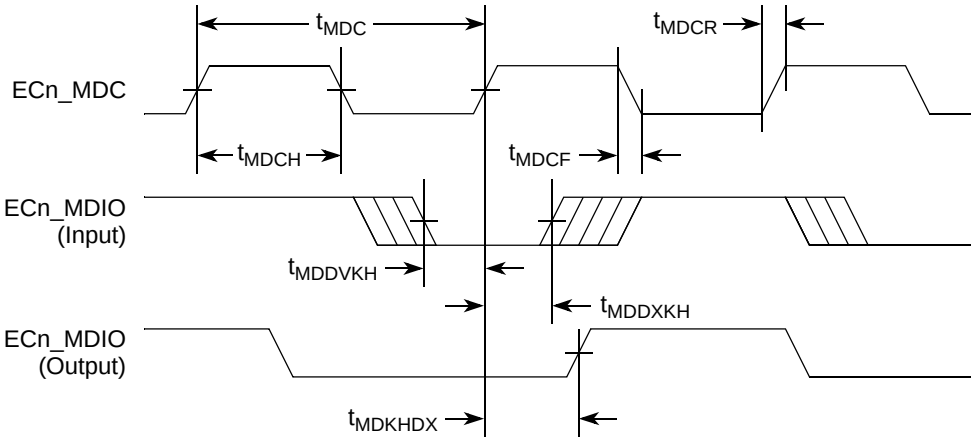


Figure 28. MII Management Interface Timing Diagram

Table 53. JTAG AC Timing Specifications (Independent of SYSCLK) [1] (continued)

At recommended operating conditions with OV_{DD} of 3.3 V ± 5%.

Parameter	Symbol [2]	Min	Max	Unit	Notes
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 3 3	 19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 36). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design.

Figure 36 provides the AC test load for TDO and the boundary-scan outputs.

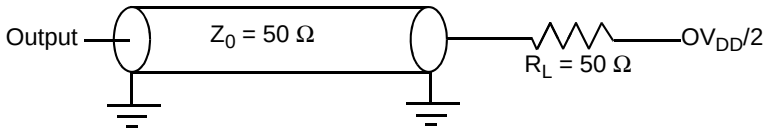


Figure 36. AC Test Load for the JTAG Interface

Figure 37 provides the JTAG clock input timing diagram.

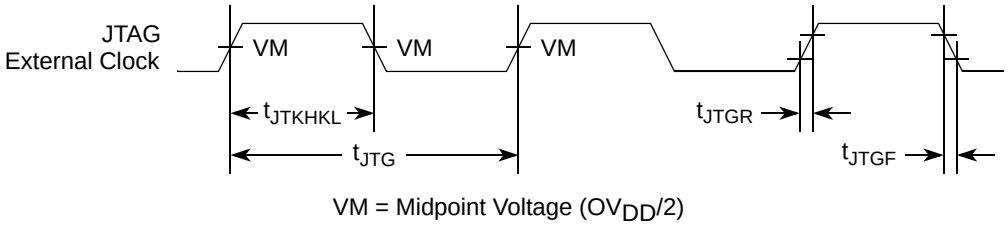


Figure 37. JTAG Clock Input Timing Diagram

Figure 38 provides the $\overline{\text{TRST}}$ timing diagram.

14 GPIO

This section describes the DC and AC electrical specifications for the GPIO interface of the MPC8572E.

14.1 GPIO DC Electrical Characteristics

Table 56 provides the DC electrical characteristics for the GPIO interface operating at BV_{DD} = 3.3 V DC.

Table 56. GPIO DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 3.3V	BV_{DD}	3.13	3.47	V
High-level input voltage	V_{IH}	2	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (BV_{IN} [1] = 0 V or BV_{IN} = BV_{DD})	I_{IN}	—	±5	μA
High-level output voltage (BV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	BV_{DD} – 0.2	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.2	V

Note:
1. Note that the symbol BV_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1.

Table 57 provides the DC electrical characteristics for the GPIO interface operating at BV_{DD} = 2.5 V DC.

Table 57. GPIO DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 2.5V	BV_{DD}	2.37	2.63	V
High-level input voltage	V_{IH}	1.70	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.7	V
Input current (BV_{IN} [1] = 0 V or BV_{IN} = BV_{DD})	I_{IH}	—	10	μA
	I_{IL}		–15	
High-level output voltage (BV_{DD} = min, I_{OH} = –1 mA)	V_{OH}	2.0	BV_{DD} + 0.3	V
Low-level output voltage (BV_{DD} min, I_{OL} = 1 mA)	V_{OL}	GND – 0.3	0.4	V

Note:
1. The symbol BV_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1.

— To meet the input amplitude requirement, the reference clock inputs might need to be DC or AC-coupled externally. For the best noise performance, the reference of the clock could be DC or AC-coupled into the unused phase (SD*n*_REF_CLK) through the same source impedance as the clock input (SD*n*_REF_CLK) in use.

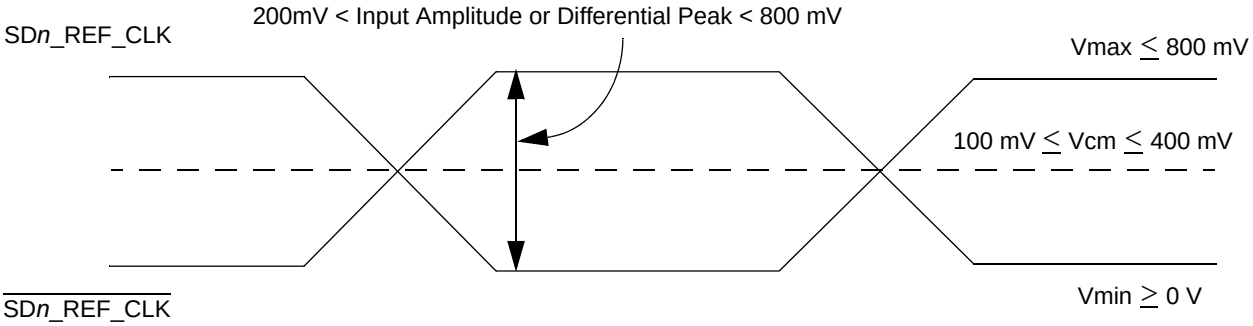


Figure 45. Differential Reference Clock Input DC Requirements (External DC-Coupled)

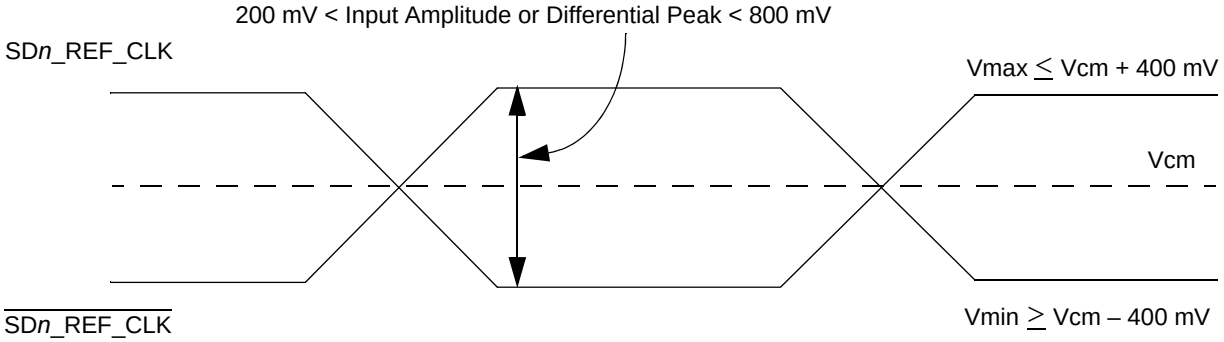


Figure 46. Differential Reference Clock Input DC Requirements (External AC-Coupled)

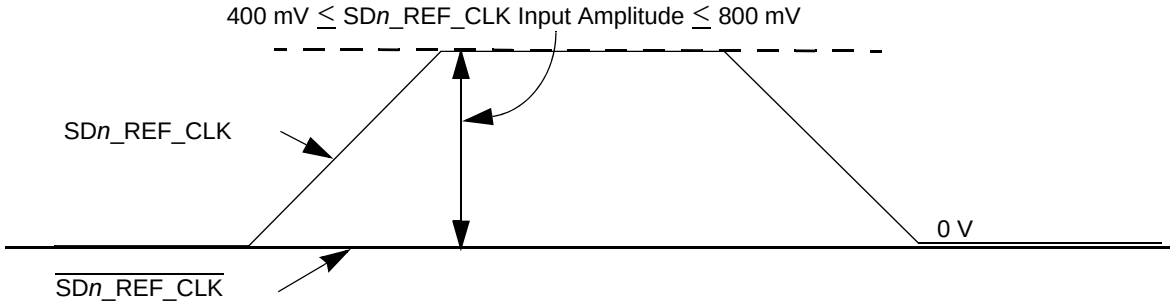


Figure 47. Single-Ended Reference Clock Input DC Requirements

16.5 Receiver Compliance Eye Diagrams

The RX eye diagram in Figure 56 is specified using the passive compliance/test measurement load (see Figure 57) in place of any real PCI Express RX component.

Note: In general, the minimum Receiver eye diagram measured with the compliance/test measurement load (see Figure 57) is larger than the minimum Receiver eye diagram measured over a range of systems at the input Receiver of any real PCI Express component. The degraded eye diagram at the input Receiver is due to traces internal to the package as well as silicon parasitic characteristics which cause the real PCI Express component to vary in impedance from the compliance/test measurement load. The input Receiver eye diagram is implementation specific and is not specified. RX component designer should provide additional margin to adequately compensate for the degraded minimum Receiver eye diagram (shown in Figure 56) expected at the input Receiver based on some adequate combination of system simulations and the Return Loss measured looking into the RX package and silicon. The RX eye diagram must be aligned in time using the jitter median to locate the center of the eye diagram.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

The reference impedance for return loss measurements is 50. to ground for both the D+ and D- line (that is, as measured by a Vector Network Analyzer with 50. probes—see Figure 57). Note that the series capacitors, CTX, are optional for the return loss measurement.

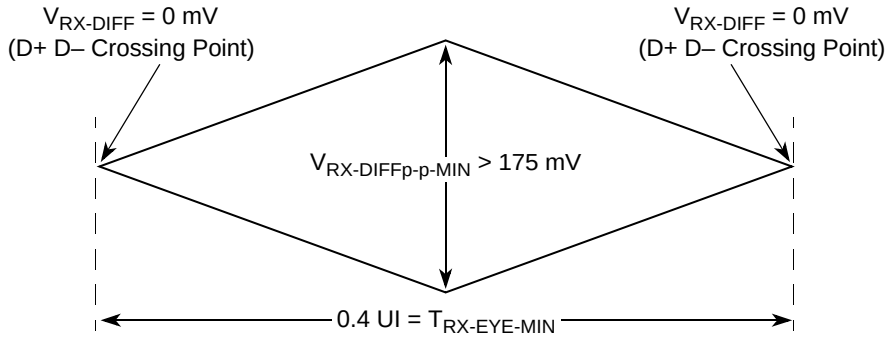


Figure 56. Minimum Receiver Eye Timing and Voltage Compliance Specification

Table 76. MPC8572E Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
D2_MBA[0:2]	Bank Select	Y1, W3, P3	O	GV_{DD}	—
$\overline{\text{D2\_MWE}}$	Write Enable	AA2	O	GV_{DD}	—
$\overline{\text{D2\_MCAS}}$	Column Address Strobe	AD1	O	GV_{DD}	—
$\overline{\text{D2\_MRAS}}$	Row Address Strobe	AA1	O	GV_{DD}	—
D2_MCKE[0:3]	Clock Enable	L3, L1, K1, K2	O	GV_{DD}	11
$\overline{\text{D2\_MCS}}$[0:3]	Chip Select	AB1, AG2, AC1, AH2	O	GV_{DD}	—
D2_MCK[0:5]	Clock	V4, F7, AJ3, V2, E7, AG4	O	GV_{DD}	—
$\overline{\text{D2\_MCK}}$[0:5]	Clock Complements	V1, F8, AJ4, U1, E6, AG5	O	GV_{DD}	—
D2_MODT[0:3]	On Die Termination	AE1, AG1, AE2, AH1	O	GV_{DD}	—
D2_MDIC[0:1]	Driver Impedance Calibration	F1, G1	I/O	GV_{DD}	25
Local Bus Controller Interface					
LAD[0:31]	Muxed Data/Address	M22, L22, F22, G22, F21, G21, E20, H22, K22, K21, H19, J20, J19, L20, M20, M19, E22, E21, L19, K19, G19, H18, E18, G18, J17, K17, K14, J15, H16, J14, H15, G15	I/O	BV_{DD}	34
LDP[0:3]	Data Parity	M21, D22, A24, E17	I/O	BV_{DD}	—
LA[27]	Burst Address	J21	O	BV_{DD}	5, 9
LA[28:31]	Port Address	F20, K18, H20, G17	O	BV_{DD}	5, 7, 9
$\overline{\text{LCS}}$[0:4]	Chip Selects	B23, E16, D20, B25, A22	O	BV_{DD}	10
$\overline{\text{LCS}}$[5]/$\overline{\text{DMA2\_DREQ}}$[1]	Chip Selects / DMA Request	D19	I/O	BV_{DD}	1, 10
$\overline{\text{LCS}}$[6]/$\overline{\text{DMA2\_DACK}}$[1]	Chip Selects / DMA Ack	E19	O	BV_{DD}	1, 10
$\overline{\text{LCS}}$[7]/$\overline{\text{DMA2\_DDONE}}$[1]	Chip Selects / DMA Done	C21	O	BV_{DD}	1, 10
$\overline{\text{LWE}}$[0]/$\overline{\text{LBS}}$[0]/$\overline{\text{LFWE}}$	Write Enable / Byte Select	D17	O	BV_{DD}	5, 9
$\overline{\text{LWE}}$[1]/$\overline{\text{LBS}}$[1]	Write Enable / Byte Select	F15	O	BV_{DD}	5, 9
$\overline{\text{LWE}}$[2]/$\overline{\text{LBS}}$[2]	Write Enable / Byte Select	B24	O	BV_{DD}	5, 9
$\overline{\text{LWE}}$[3]/$\overline{\text{LBS}}$[3]	Write Enable / Byte Select	D18	O	BV_{DD}	5, 9
LALE	Address Latch Enable	F19	O	BV_{DD}	5, 8, 9
LBCTL	Buffer Control	L18	O	BV_{DD}	5, 8, 9

Table 76. MPC8572E Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
SD1_RX[7:0]	Receive Data (positive)	P32, N30, M32, L30, G30, F32, E30, D32	I	XV_{DD_SRDS1}	—
$\overline{\text{SD1\_RX}}$[7:0]	Receive Data (negative)	P31, N29, M31, L29, G29, F31, E29, D31	I	XV_{DD_SRDS1}	—
SD1_TX[7]	PCIe1 Tx Data Lane 7 / SRIO or PCIe2 Tx Data Lane 3 / PCIe3 TX Data Lane 1	M26	O	XV_{DD_SRDS1}	—
SD1_TX[6]	PCIe1 Tx Data Lane 6 / SRIO or PCIe2 Tx Data Lane 2 / PCIe3 TX Data Lane 0	L24	O	XV_{DD_SRDS1}	—
SD1_TX[5]	PCIe1 Tx Data Lane 5 / SRIO or PCIe2 Tx Data Lane 1	K26	O	XV_{DD_SRDS1}	—
SD1_TX[4]	PCIe1 Tx Data Lane 4 / SRIO or PCIe2 Tx Data Lane 0	J24	O	XV_{DD_SRDS1}	—
SD1_TX[3]	PCIe1 Tx Data Lane 3	G24	O	XV_{DD_SRDS1}	—
SD1_TX[2]	PCIe1 Tx Data Lane 2	F26	O	XV_{DD_SRDS1}	—
SD1_TX[1]	PCIe1 Tx Data Lane 1]	E24	O	XV_{DD_SRDS1}	—
SD1_TX[0]	PCIe1 Tx Data Lane 0	D26	O	XV_{DD_SRDS1}	—
$\overline{\text{SD1\_TX}}$[7:0]	Transmit Data (negative)	M27, L25, K27, J25, G25, F27, E25, D27	O	XV_{DD_SRDS1}	—
SD1_PLL_TPD	PLL Test Point Digital	J32	O	XV_{DD_SRDS1}	17
SD1_REF_CLK	PLL Reference Clock	H32	I	XV_{DD_SRDS1}	—
$\overline{\text{SD1\_REF\_CLK}}$	PLL Reference Clock Complement	H31	I	XV_{DD_SRDS1}	—
Reserved	—	C29, K32	—	—	26
Reserved	—	C30, K31	—	—	27
Reserved	—	C24, C25, H26, H27	—	—	28
Reserved	—	AL20, AL21	—	—	29
SerDes (x4) SGMII					
SD2_RX[3:0]	Receive Data (positive)	AK32, AJ30, AF30, AE32	I	XV_{DD_SRDS2}	—

Table 85 summarizes the signal impedance targets. The driver impedances are targeted at minimum V_{DD}, nominal OV_{DD}, 105°C.

Table 85. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	DDR DRAM	Symbol	Unit
R_N	45 Target	18 Target (full strength mode) 36 Target (half strength mode)	Z_0	Ω
R_P	45 Target	18 Target (full strength mode) 36 Target (half strength mode)	Z_0	Ω

Note: Nominal supply voltages. See Table 1, T_j = 105°C.

21.8 Configuration Pin Muxing

The MPC8572E provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of 4.7 kΩ on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

While $\overline{\text{HRESET}}$ is asserted however, these pins are treated as inputs. The value presented on these pins while $\overline{\text{HRESET}}$ is asserted, is latched when $\overline{\text{HRESET}}$ deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Most of these sampled configuration pins are equipped with an on-chip gated resistor of approximately 20 kΩ. This value should permit the 4.7-kΩ resistor to pull the configuration pin to a valid logic low level. The pull-up resistor is enabled only during $\overline{\text{HRESET}}$ (and for platform /system clocks after $\overline{\text{HRESET}}$ deassertion to ensure capture of the reset value). When the input receiver is disabled the pull-up is also, thus allowing functional operation of the pin as an output with minimal signal quality or delay disruption. The default value for all configuration bits treated this way has been encoded such that a high voltage level puts the device into the default state and external resistors are needed only when non-default settings are required by the user.

Careful board layout with stubless connections to these pull-down resistors coupled with the large value of the pull-down resistor should minimize the disruption of signal quality or speed for output pins thus configured.

The platform PLL ratio, DDR complex PLL and e500 PLL ratio configuration pins are not equipped with these default pull-up devices.

21.9 JTAG Configuration Signals

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 66. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion gives unpredictable results.

Boundary-scan testing is enabled through the JTAG interface signals. The $\overline{\text{TRST}}$ signal is optional in the IEEE Std 1149.1 specification, but it is provided on all processors built on Power Architecture technology. The device requires $\overline{\text{TRST}}$ to be asserted during power-on reset flow to ensure that the JTAG boundary

logic does not interfere with normal chip operation. While the TAP controller can be forced to the reset state using only the TCK and TMS signals, generally systems assert $\overline{\text{TRST}}$ during the power-on reset flow. Simply tying $\overline{\text{TRST}}$ to $\overline{\text{HRESET}}$ is not practical because the JTAG interface is also used for accessing the common on-chip processor (COP), which implements the debug interface to the chip.

The COP function of these processors allow a remote computer system (typically, a PC with dedicated hardware and debugging software) to access and control the internal operations of the processor. The COP interface connects primarily through the JTAG port of the processor, with some additional status monitoring signals. The COP port requires the ability to independently assert $\overline{\text{HRESET}}$ or $\overline{\text{TRST}}$ to fully control the processor. If the target system has independent reset sources, such as voltage monitors, watchdog timers, power supply failures, or push-button switches, then the COP reset signals must be merged into these signals with logic.

The arrangement shown in Figure 66 allows the COP port to independently assert $\overline{\text{HRESET}}$ or $\overline{\text{TRST}}$, while ensuring that the target can drive $\overline{\text{HRESET}}$ as well.

The COP interface has a standard header, shown in Figure 65, for connection to the target system, and is based on the 0.025" square-post, 0.100" centered header assembly (often called a Berg header). The connector typically has pin 14 removed as a connector key.

The COP header adds many benefits such as breakpoints, watchpoints, register and memory examination/modification, and other standard debugger features. An inexpensive option can be to leave the COP header unpopulated until needed.

There is no standardized way to number the COP header; so emulator vendors have issued many different pin numbering schemes. Some COP headers are numbered top-to-bottom then left-to-right, while others use left-to-right then top-to-bottom. Still others number the pins counter-clockwise from pin 1 (as with an IC). Regardless of the numbering scheme, the signal placement recommended in Figure 65 is common to all known emulators.

21.9.1 Termination of Unused Signals

If the JTAG interface and COP header is not used, Freescale recommends the following connections:

- $\overline{\text{TRST}}$ should be tied to $\overline{\text{HRESET}}$ through a 0 kΩ isolation resistor so that it is asserted when the system reset signal ($\overline{\text{HRESET}}$) is asserted, ensuring that the JTAG scan chain is initialized during the power-on reset flow. Freescale recommends that the COP header be designed into the system as shown in Figure 66. If this is not possible, the isolation resistor allows future access to $\overline{\text{TRST}}$ in case a JTAG interface may need to be wired onto the system in future debug situations.
- No pull-up/pull-down is required for TDI, TMS, TDO or TCK.

22 Ordering Information

Ordering information for the parts fully covered by this specification document is provided in Section 22.1, “Part Numbers Fully Addressed by this Document.”

22.1 Part Numbers Fully Addressed by this Document

Table 86 through Table 88 provide the Freescale part numbering nomenclature for the MPC8572E. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. In addition to the processor frequency, the part numbering scheme also includes an application modifier which may specify special application conditions. Each part number also contains a revision code which refers to the die mask revision number.

Table 86. Part Numbering Nomenclature—Rev 2.2.1

MPC	*nnnn*	*e*	*t*	*l*	*pp*	*ffm*	*r*
Product Code[1]	**Part Identifier**	**Security Engine**	**Temperature**	**Power**	**Package Sphere Type[2]**	**Processor Frequency/ DDR Data Rate[3]**	**Silicon Revision**
MPC PPC	8572	E = Included	Blank = 0 to 105°C C = –40 to 105°C	Blank = Standard L = Low	PX = Leaded, FC-PBGA VT = Pb-free, FC-PBGA[4] VJ = Fully Pb-free FC-PBGA[5]	AVN = 1500-MHz processor; 800 MT/s DDR data rate AUL = 1333-MHz processor; 667 MT/s DDR data rate ATL = 1200-MHz processor; 667 MT/s DDR data rate ARL = 1067-MHz processor; 667 MT/s DDR data rate	E = Ver. 2.2.1 (SVR = 0x80E8_0022) SEC included
		Blank = Not included					E = Ver. 2.2.1 (SVR = 0x80E0_0022) SEC not included

Notes:

1 MPC stands for “Qualified.”
PPC stands for “Prototype”

2 See Section 18, “Package Description,” for more information on the available package types.

3 Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.

4. The VT part number is ROHS-compliant with the permitted exception of the C4 die bumps.

5. The VJ part number is entirely lead-free. This includes the C4 die bumps.